

## 2010 —FUJIWARA Yasufumi

### Scientific Papers/Commentary Articles

1. H. Ohta, O. Portugall, N. Ubrig, M. Fujisawa, H. Katsuno, E. Fatma, S. Okubo, and Y. Fujiwara, Photoluminescence measurement of Er,O-codoped GaAs under a pulsed magnetic field up to 60 T, *Journal of Low Temperature Physics*, 159, 203-207, 2010
2. M. Fujisawa, A. Asakura, F. Elmasry, S. Okubo, H. Ohta, and Y. Fujiwara, Magnetic properties of magnetic semiconductor GaAs:Er,O studied by ESR, *Journal of Physics: Conference Series*, 200, 062005/1-4, 2010
3. Y. Fujiwara, A. Nishikawa, and Y. Terai, Rare-earth-doped semiconductor-based light-emitting diodes operating at room temperature, *e-Journal of Light Emitting Diode*, 2(1), W-II-2/1-4, 2010
4. Y. Konaka, K. Ono, Y. Terai, and Y. Fujiwara, Coexistence properties of phase separation and CuPt-ordering in InGaAsP grown on GaAs substrates by organometallic vapor phase epitaxy, *Journal of Crystal Growth*, 312, 2056-2059, 2010
5. A. Nishikawa, T. Kawasaki, N. Furukawa, Y. Terai, and Y. Fujiwara, Low-voltage operation of current-injection red emission from p-GaN/Eu-doped GaN/n-GaN light-emitting diodes, *Physica Status Solidi A*, 207(6), 1397–1399, 2010
6. T. Kawasaki, N. Furukawa, A. Nishikawa, Y. Terai, and Y. Fujiwara, Effect of growth temperature on Eu-doped GaN layers grown by organometallic vapor phase epitaxy, *Physica Status Solidi C*, 7(7-8), 2040-2042, 2010
7. A. Nishikawa, N. Furukawa, T. Kawasaki, Y. Terai, and Y. Fujiwara, Improved luminescence properties of Eu-doped GaN light-emitting diodes grown by atmospheric-pressure organometallic vapor phase epitaxy, *Applied Physics Letters*, 97(5), 051113/1-3, 2010
8. K. Lorenz, E. Alves, I. S. Roqan, K. P. O'Donnell, A. Nishikawa, Y. Fujiwara, and M. Bockowski, Lattice site location of optical centres in GaN:Eu LED material grown by organometallic vapor phase epitaxy, *Applied Physics Letters*, 97(11), 111911/1-3, 2010
9. A. Nishikawa, T. Kawasaki, N. Furukawa, Y. Terai, and Y. Fujiwara, Growth temperature dependence of Eu-doped GaN grown by organometallic vapor phase epitaxy, *Journal of The Society of Materials Science Japan*, 59(9), 671-674, 2010
10. Y. Terai, K. Yoshida, and Y. Fujiwara, Photoluminescence properties of Eu-doped ZnO grown by sputtering-assisted metalorganic chemical vapor deposition, *Journal of The Society of Materials Science Japan*, 59(10), 690-693, 2010
11. Y. Terai, T. Tsuji, K. Noda, and Y. Fujiwara, Photoluminescence properties of Er-doped  $\beta$ -FeSi<sub>2</sub> grown by ion beam synthesis methods, *Physica E*, 42, 2846–2848, 2010
12. Y. Terai, K. Yamaoka, K. Yoshida, A. Yoshida, and Y. Fujiwara, Photoluminescence properties of

- Eu-doped ZnO films grown by sputtering-assisted metalorganic chemical vapor deposition, *Physica E*, 42, 2834–2836., 2010
13. N. Furukawa, A. Nishikawa, T. Kawasaki, Y. Terai, and Y. Fujiwara, Atmospheric pressure growth of Eu-doped GaN by organometallic vapor phase epitaxy, *Physica Status Solidi A*, 208(2), 445-448, 2011
  14. Y. Terai, K. Yoshida, M. H. Kamarudin, and Y. Fujiwara, Photoluminescence properties of Eu<sup>3+</sup> ions in Eu-doped ZnO grown by sputtering-assisted metalorganic chemical vapor deposition, *Physica Status Solidi C*, 8(2), 519-521, 2011
  15. H. Ofuchi, T. Honma, A. Nishikawa, N. Furukawa, T. Kawasaki, and Y. Fujiwara, Fluorescence EXAFS analysis of Eu-doped GaN layers grown by organometallic vapor phase epitaxy, *e-Journal of Surface Science and Nanotechnology*, 9, 51-53, 2011
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  17. K. Yoneda, Y. Terai, K. Noda, N. Miura, and Y. Fujiwara, Photoluminescence and photorefectance studies in Si/ $\beta$ -FeSi<sub>2</sub>/Si(001) double heterostructure, *Physics Procedia*, 11, 185-188, 2011
  18. M. Fujisawa, A. Asakura, F. Elmasry, S. Okubo, H. Ohta, and Y. Fujiwara, ESR study of photoluminescent material GaAs:Er,O -Er concentration effect-, *Journal of Applied Physics*, 109(5), 053910/1-5, 2011